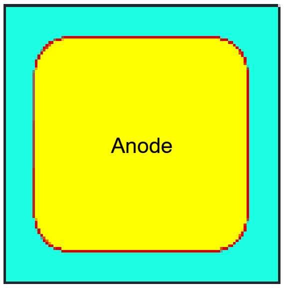
FFSH5065A-DIE

Silicon Carbide Schottky Diode

650 V, 50 A

ON Semiconductor®

www.onsemi.com



ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature dependent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 240 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

Die Information

- Wafer Diameter: 6 inch
- Die Size: 3,350 × 3,350 μm (include Scribe Lane)
- Metallization:
  - Top 40KA 0.5%AlCu
  - Back 0.5K Ti + 3K Ni/V + 1.5K Ag
- Die Thickness: Typ. 200 μm
- Bonding Pad Size
  - Anode 2,990 × 2,990 μm
- Recommended Wire Bond (Note 1)
  - Anode: 20 mil × 3

ELECTRICAL CHARACTERISTICS ON WAFER (T_C = 25°C unless otherwise noted) (Note 2)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V_R	Reverse Blocking Voltage	I_R = 200 μA, T_C = 25°C	650	–	–	V
V_F	Forward Voltage	I_F = 50 A, T_C = 25°C	1.20	–	1.75	V
I_R	Reverse Current	V_R = 650 V, T_C = 25°C	–	–	200	μA

NOTES:
1. Based on TO−220 package of ON Semiconductor.
2. Tested 100% on wafer.

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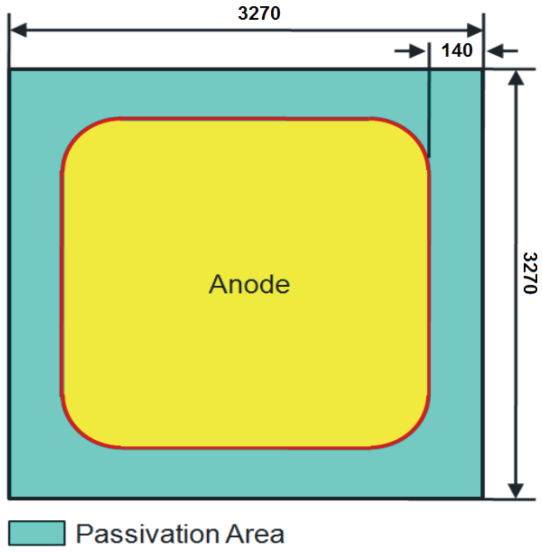
Die Layout



(Dimensions: µm, except Scribe Lane)

Figure 1. Die Layout

Cross Section

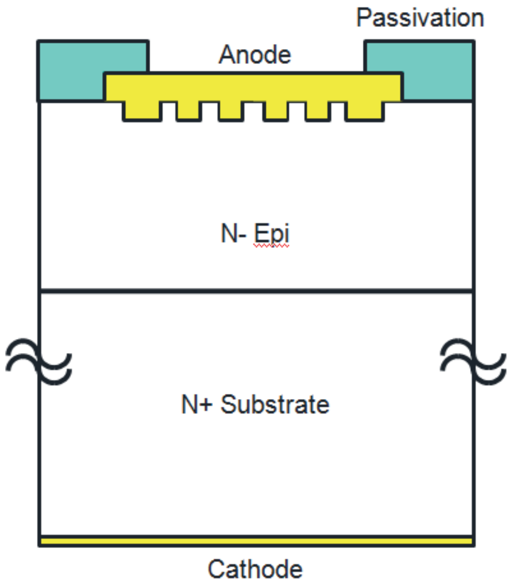


Figure 2. Cross Section

Passivation Information

- Passivation Material: Polymide (PSPI)
- Passivation Type: Local Passivation
- Passivation Thickness: 90 KA

The Configuration of Chips (Based on 6″ Wafer)

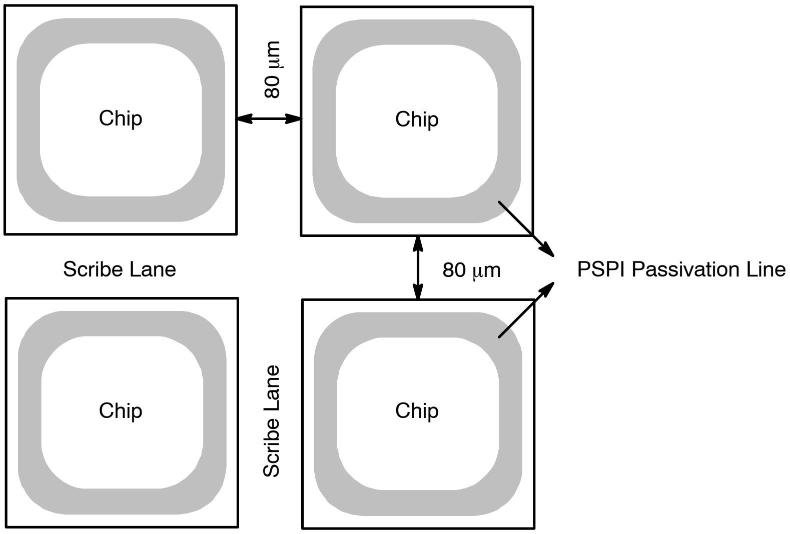


Figure 3. Saw-on-film Frame Packing Based on Tested Wafer

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage		650	V
E_{AS}	Single Pulse Avalanche Energy (Note 3)		240	mJ
I_F	Continuous Rectified Forward Current @ $T_C < 144°C$		50	A
	Continuous Rectified Forward Current @ $T_C < 135°C$		60	
$I_{F,\ Max}$	Non-Repetitive Peak Forward Surge Current	T_C = 25°C, 10 μs	1350	A
		T_C = 150°C, 10 μs	1250	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t_p = 8.3 ms	230	A
$I_{F,RM}$	Repetitive Forward Surge Current	Half-Sine Pulse, t_p = 8.3 ms	95	A
Ptot	Power Dissipation	T_C = 25°C	429	W
		T_C = 150°C	72	W
T_J, T_{STG}	Operating and Storage Temperature Range		−55 to +175	°C
	TO−247 Mounting Torque, M3 Screw		60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

3. E_{AS} of 240 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 31 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.35	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V_F	Forward Voltage	I_F = 50 A, T_C = 25°C	–	1.51	1.75	V
		I_F = 50 A, T_C = 125°C	–	1.67	2.0	
		I_F = 50 A, T_C = 175°C	–	1.82	2.4	
I_R	Reverse Current	V_R = 650 V, T_C = 25°C	–	–	200	μA
		V_R = 650 V, T_C = 125°C	–	–	400	
		V_R = 650 V, T_C = 175°C	–	–	600	
Q_C	Total Capacitive Charge	V = 400 V	–	147	–	nC
C	Total Capacitance	V_R = 1 V, f = 100 kHz	–	2530	–	pF
		V_R = 200 V, f = 100 kHz	–	271	–	
		V_R = 400 V, f = 100 kHz	–	211	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse: Test Pulse width = 300 μs, Duty Cycle = 2%.

ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Quantity
PCFFS5065AF	No Marking	TBD	TBD	TBD

TYPICAL CHARACTERISTICS

(T_J = 25°C unless otherwise noted)

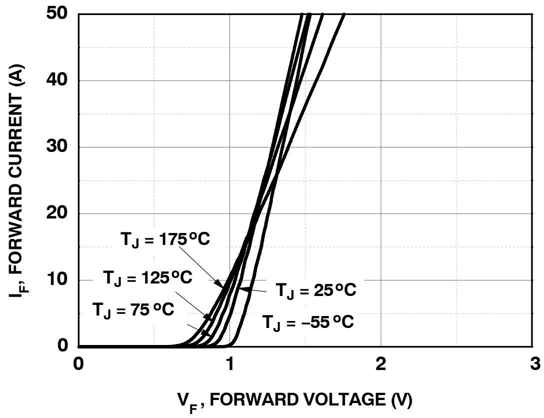


Figure 4. Forward Characteristics

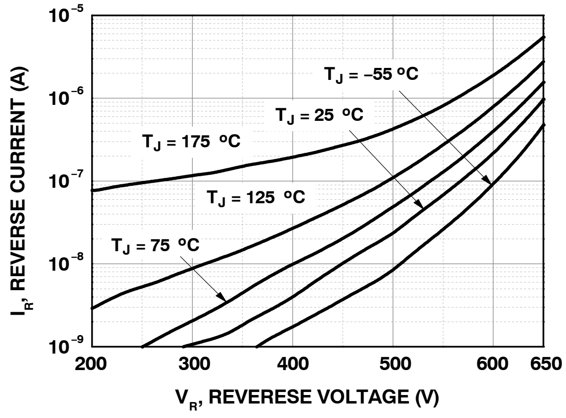


Figure 5. Reverse Characteristics

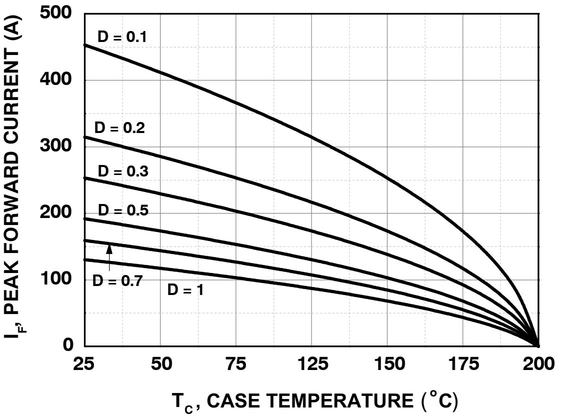


Figure 6. Current Derating

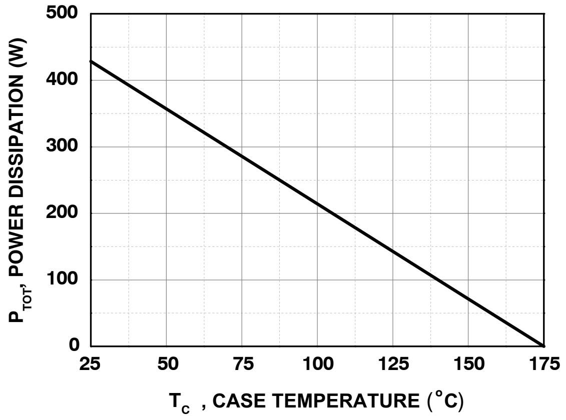


Figure 7. Power Derating

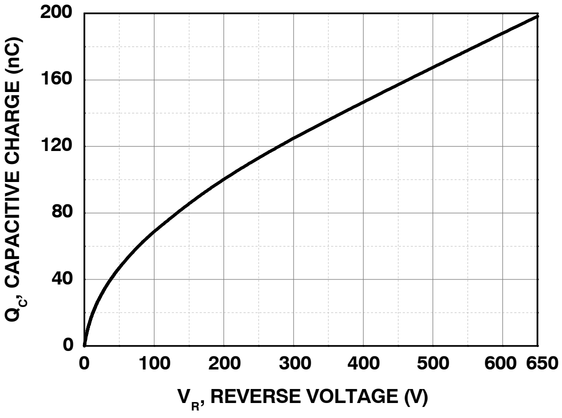


Figure 8. Capacitive Charge vs. Reverse Voltage

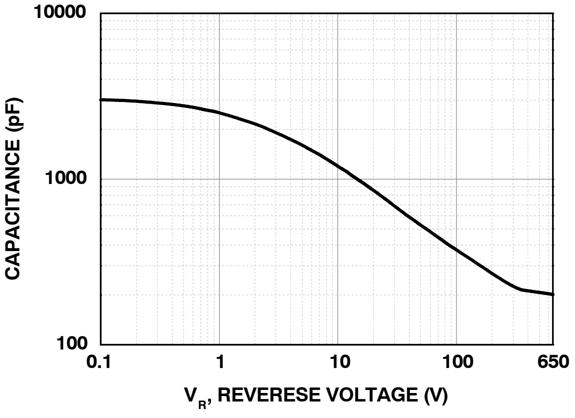


Figure 9. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS

(T_J = 25°C unless otherwise noted)

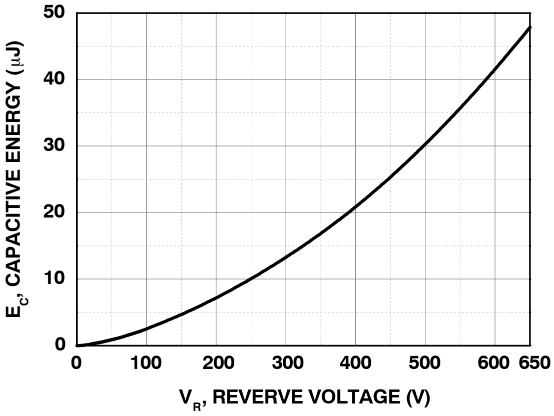


Figure 10. Capacitance Stored Energy

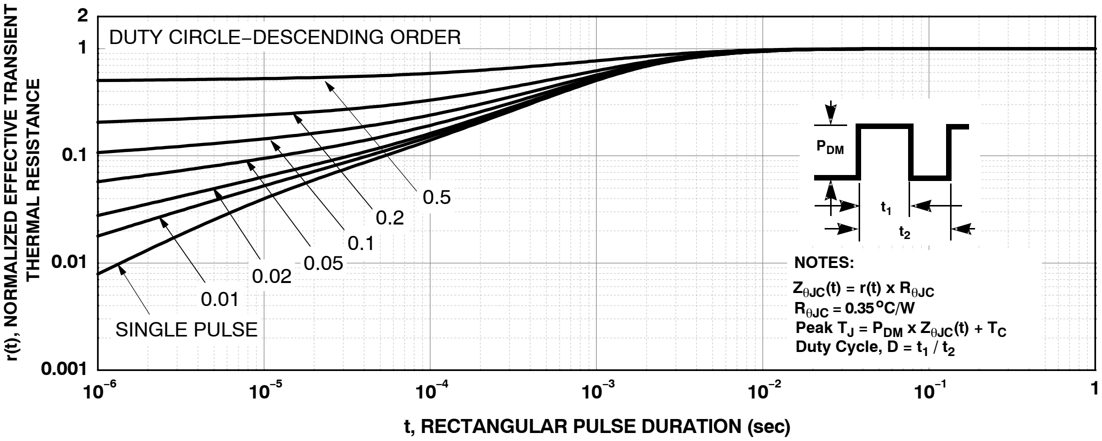


Figure 11. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

$L = 0.5$ mH
$R < 0.1\ \Omega$
$V_{DD} = 50$ V
$EAVL = 1/2LI2\ [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$
$Q1 = \text{IGBT}\ (BV_{CES} > \text{DUT}\ V_{R(AVL)})$

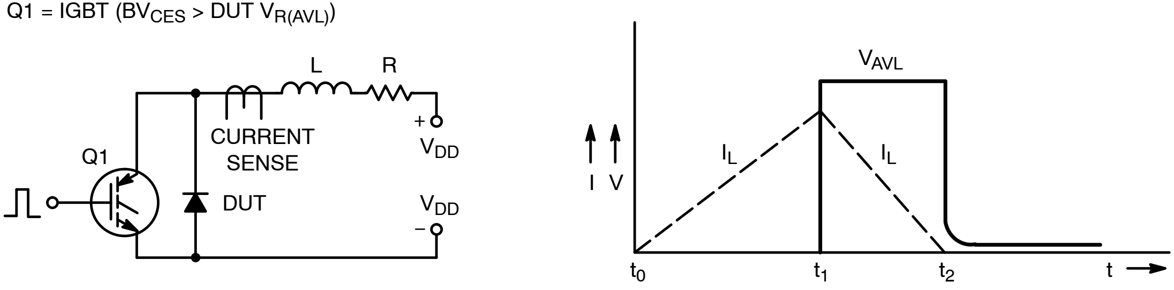


Figure 12. Unclamped Inductive Switching Test Circuit & Waveform

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